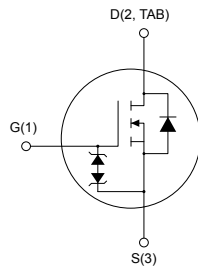
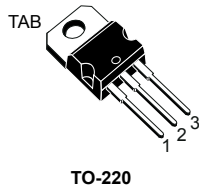


## N-channel 800 V, 0.470 $\Omega$ typ., 9 A MDmesh™ K5 Power MOSFET in a TO-220 package



AM01475V1

### Features

Order code	$V_{DS}$	$R_{DS(on)}$ max.	$I_D$	$P_{TOT}$
STP10N80K5	800 V	0.600 $\Omega$	9 A	130 W

- Industry's lowest  $R_{DS(on)}$  x area
- Industry's best FoM (figure of merit)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

### Applications

- Switching applications

### Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Product status	
STP10N80K5	
Product summary	
<b>Order code</b>	STP10N80K5
<b>Marking</b>	10N80K5
<b>Package</b>	TO-220
<b>Packing</b>	Tube

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 30$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	9	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	6	A
$I_{DM}^{(1)}$	Drain current pulsed	36	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	130	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	
$T_j$	Operating junction temperature range	- 55 to 150	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		

1. Pulse width limited by safe operating area.
2.  $I_{SD} \leq 9\text{ A}$ ,  $di/dt \leq 100\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} \leq V_{(BR)DSS}$
3.  $V_{DS} \leq 640\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.96	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	$^\circ\text{C}/\text{W}$

**Table 3. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax.}$ )	3	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	130	mJ

## 2 Electrical characteristics

$T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified

**Table 4. On/off-state**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	800			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 800\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}, V_{DS} = 800\text{ V}$ $T_C = 125\text{ }^\circ\text{C}^{(1)}$			50	$\mu\text{A}$
$I_{GSS}$	Gate body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$		0.470	0.600	$\Omega$

1. Defined by design, no subject to production test.

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0\text{ V}$	-	635	-	pF
$C_{oss}$	Output capacitance		-	53	-	pF
$C_{rss}$	Reverse transfer capacitance		-	0.8	-	pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }640\text{ V}, V_{GS} = 0\text{ V}$	-	85	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related		-	34	-	pF
$R_g$	Intrinsic gate resistance	$f = 1\text{ MHz}, I_D = 0\text{ A}$	-	6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 640\text{ V}, I_D = 9\text{ A}$	-	22	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	5.5	-	nC
$Q_{gd}$	Gate-drain charge	(see Figure 15. Test circuit for gate charge behavior)	-	13.2	-	nC

1.  $C_{o(tr)}$  is a constant capacitance value that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

2.  $C_{o(er)}$  is a constant capacitance value that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Table 6. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}, I_D = 4.5\text{ A}, R_G = 4.7\text{ }\Omega$	-	14.5	-	ns
$t_r$	Rise time		-	11	-	ns
$t_{d(off)}$	Turn-off delay time	$V_{GS} = 10\text{ V}$ (see Figure 14. Test circuit for resistive load switching times and Figure 19. Switching time waveform)	-	35	-	ns
$t_f$	Fall time		-	14	-	ns

**Table 7. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		36	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 9\text{ A}$ , $V_{GS} = 0\text{ V}$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,	-	370		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ , see <a href="#">Figure 16. Test circuit for inductive load switching and diode recovery times</a>	-	4.58		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	25		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ ,	-	520		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$	-	5.88		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see <a href="#">Figure 16. Test circuit for inductive load switching and diode recovery times</a> )	-	22.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

**Table 8. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ , $I_D = 0\text{ A}$	$\pm 30$	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

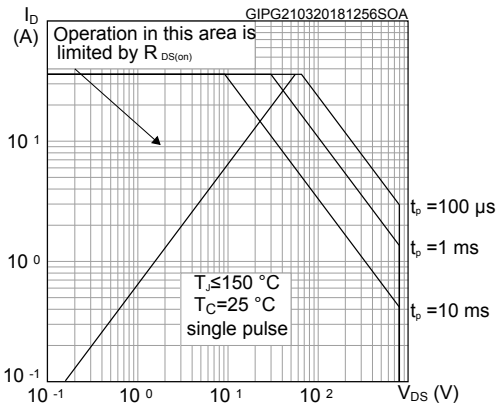


Figure 2. Thermal impedance

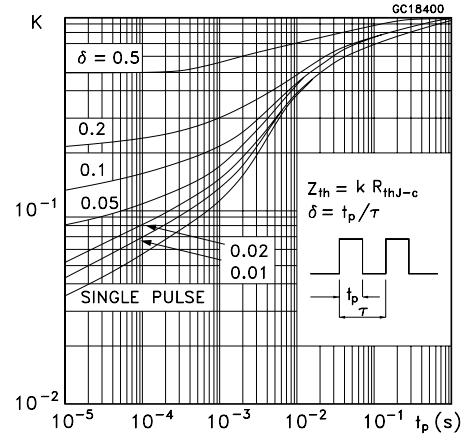


Figure 3. Output characteristics

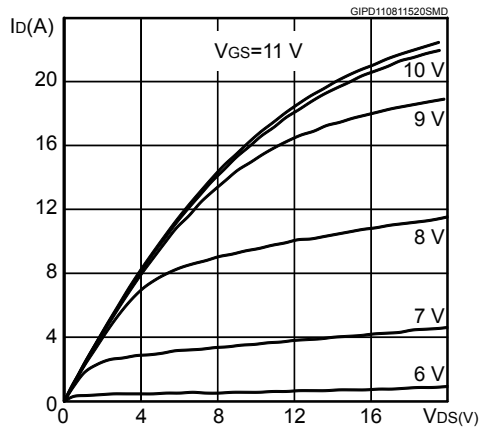


Figure 4. Transfer characteristics

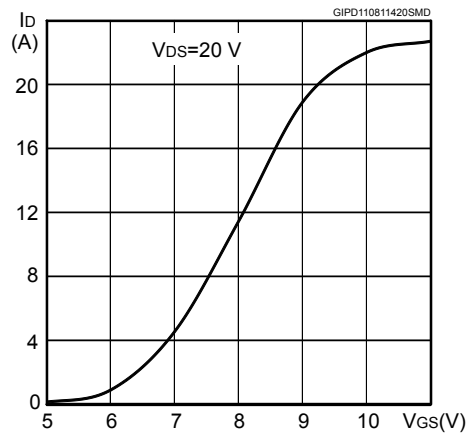


Figure 5. Gate charge vs. gate-source voltage

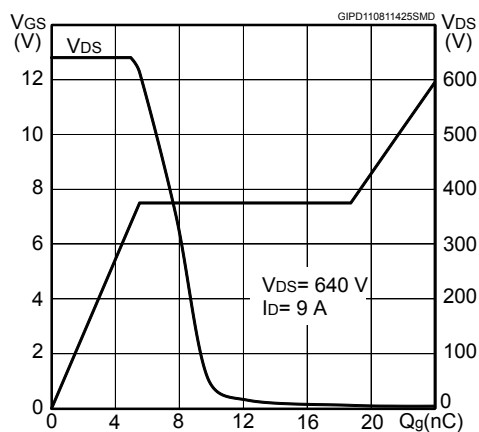


Figure 6. Static drain-source on-resistance

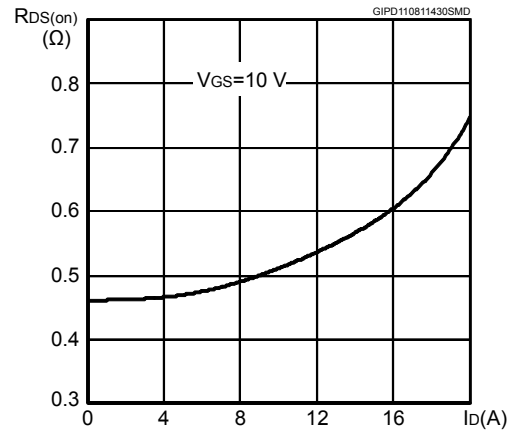


Figure 7. Capacitance variations

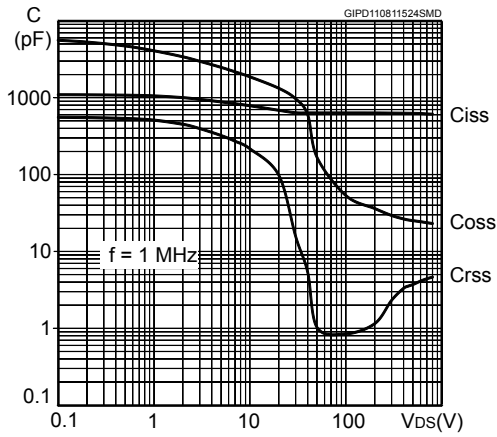


Figure 8. Source-drain diode forward characteristics

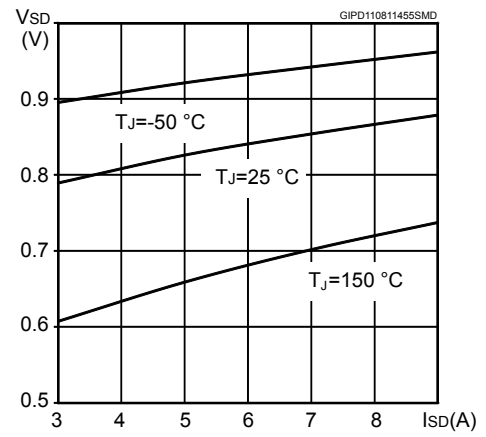


Figure 9. Normalized gate threshold voltage vs. temperature

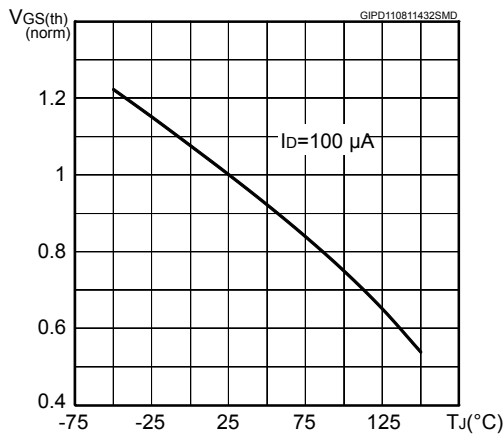


Figure 10. Normalized on-resistance vs. temperature

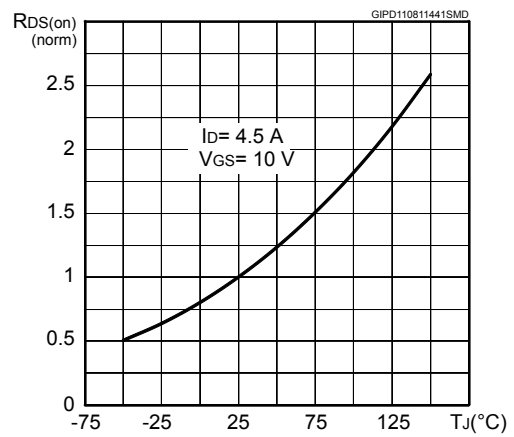


Figure 11. Normalized V<sub>(BR)DSS</sub> vs. temperature

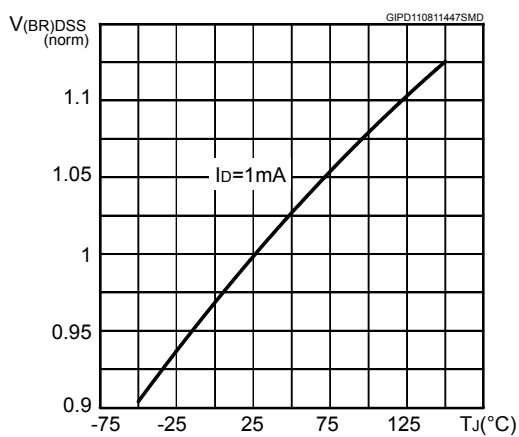


Figure 12. Maximum avalanche energy vs. starting T<sub>J</sub>

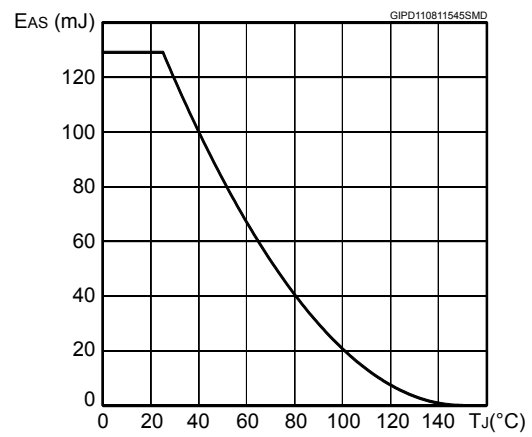
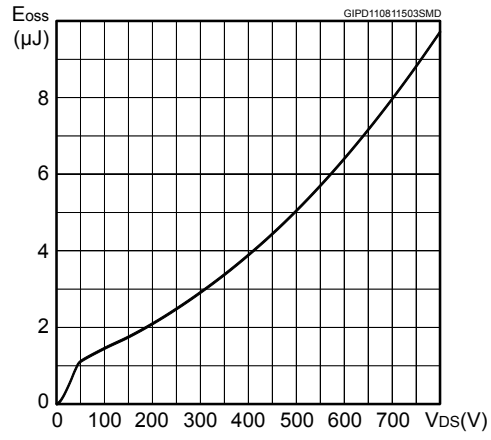
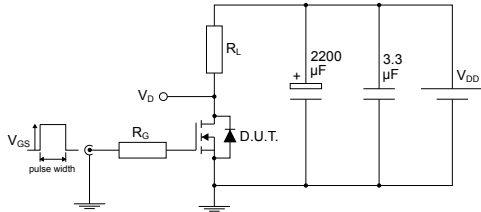


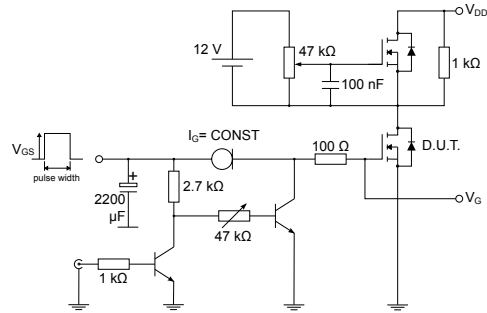
Figure 13. Output capacitance stored energy



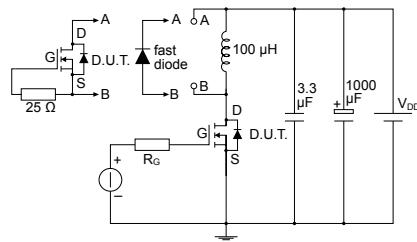
### 3 Test circuits

**Figure 14. Test circuit for resistive load switching times**


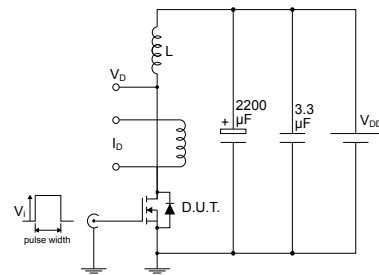
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**Figure 15. Test circuit for gate charge behavior**


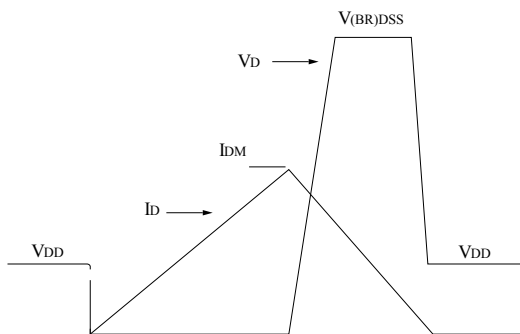
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**Figure 16. Test circuit for inductive load switching and diode recovery times**


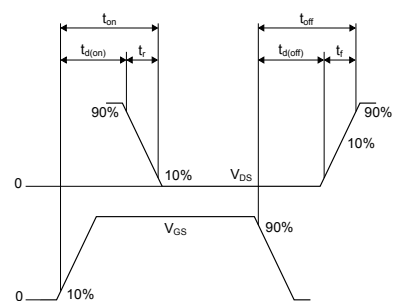
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**Figure 17. Unclamped inductive load test circuit**


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**Figure 18. Unclamped inductive waveform**


AM01472v1

**Figure 19. Switching time waveform**


AM01473v1



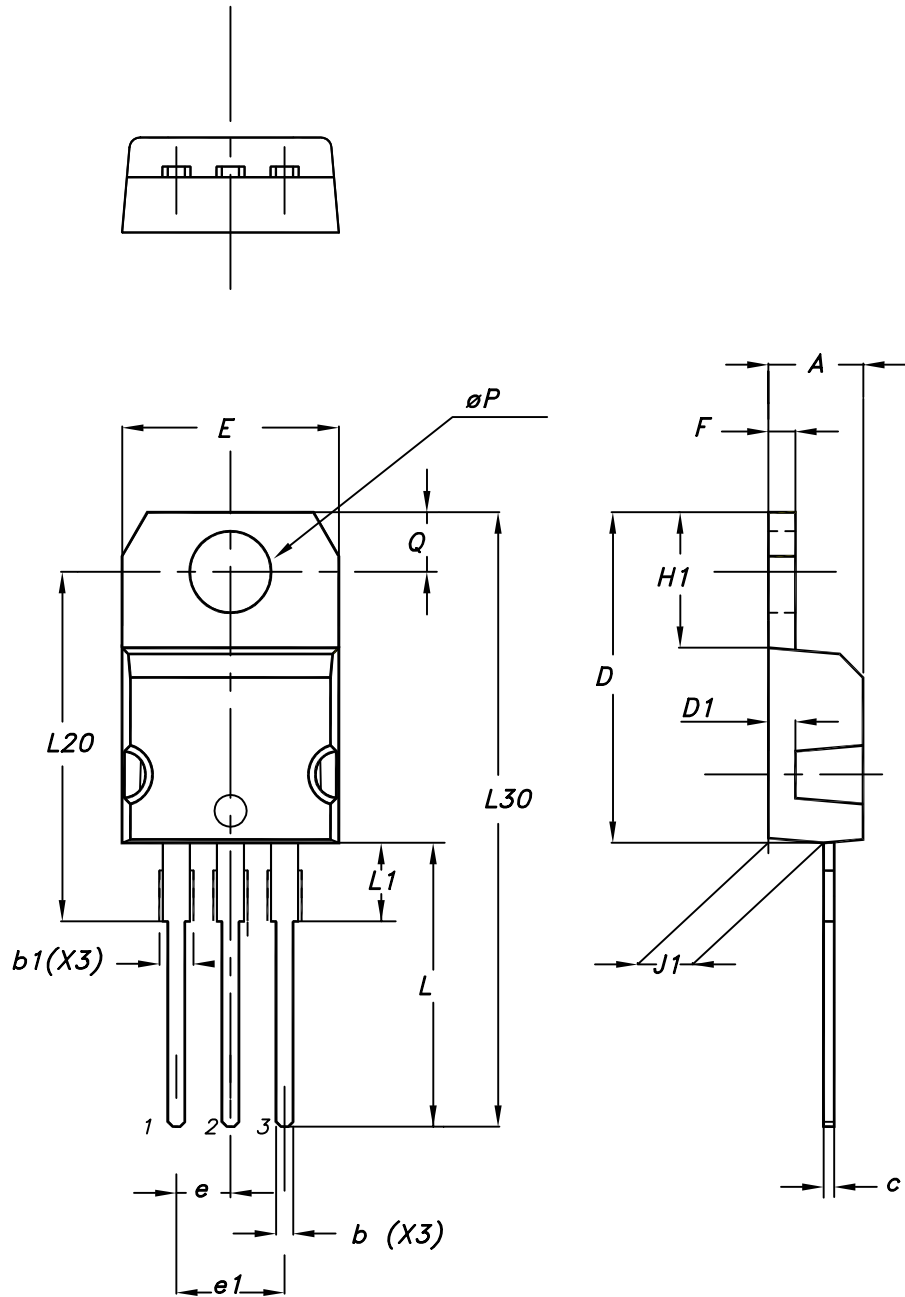
## 4 Package information

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In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-220 type A package information

Figure 20. TO-220 type A package outline



0015988\_typeA\_Rev\_21

**Table 9. TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

## Revision history

**Table 10. Document revision history**

Date	Revision	Changes
21-Mar-2018	1	Initial release. The document status is production data.

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